

areas on the optical mask with different light  
 penetration capability), a plurality of dummies is  
 generated at the bottom of the chosen shallow trenches  
 at the time the shallow trenches are first formed. Please  
 5 refer to Fig.12. Fig.12 shows the second method of  
 forming dummies according to the present invention.  
 In this scheme, one mask photo is used to place an optical  
 mask 60 above the semiconductor wafer 30 and to expose  
 and transfer patterns by using different light  
 10 penetration capability on the optical mask 60. The  
 surface of the semiconductor wafer 30 comprises a Si  
 substrate 34, a pad oxide layer 36, a pad nitride layer  
 38 and a negative photoresist layer 62. The optical  
 mask 60 comprises a plurality of areas (the space parts)  
 15 of which the light penetration capability is 100%, a  
 plurality of areas (the parts with oblique lines) of  
 which the light penetration capability is 0% and a  
 plurality of areas (the parts with horizontal lines)  
 of which the light penetration capability is between  
 20 0% to 100%; therefore, the corresponding photoresists  
 64 are either completely dissolved, not dissolved at  
 all or partly dissolved on the negative photoresist  
 layer 62 of semiconductor wafer 30 and used as masks.  
 Thus, after etching is repeated, the semiconductor  
 25 wafer 30 with a plurality of dummies and shallow trenches,  
 as shown in Fig.11, is made.

2. On page 7, lines 16-31, and page 8, lines 1-9, please  
 replace the paragraph with the following:

30

Please refer to Fig.13 and Fig.14. Fig.13 and  
 Fig.14 show the third method of forming dummies